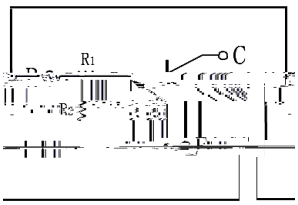
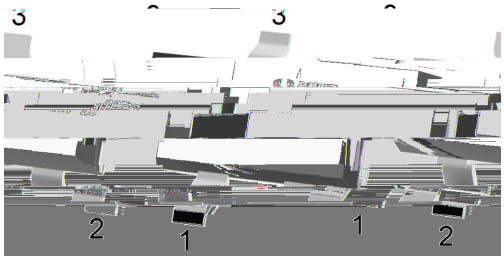
VRW056 ɱɱ Ƭ SQS ʺǪ È s ǁ ᒣ Silicon PNP Digital transistor in a SOT-23 Plastic Package.

ɲ Ƭ ə ɹ ɔ ɠ ı ᐯ ƥ ɻ ب ɸ ɰ ı ᵒ ᵒ N̲ ƒ ʈ ⁼ · ʓ ╙ ʏ ı ɳ ɾ β
With built-in bias resistors, simplify circuit design, reduce a quantity of parts and manufacturing process,HF Product.

ᵮ Â ʜ ɾ ᵔ ɔ ب ɳ ᵶ ɔ ب Ⓠ ȝ ɨ ʊ ɔ ب ᴀ
Switching, inverter circuit, interface circuit and driver circuit applications.



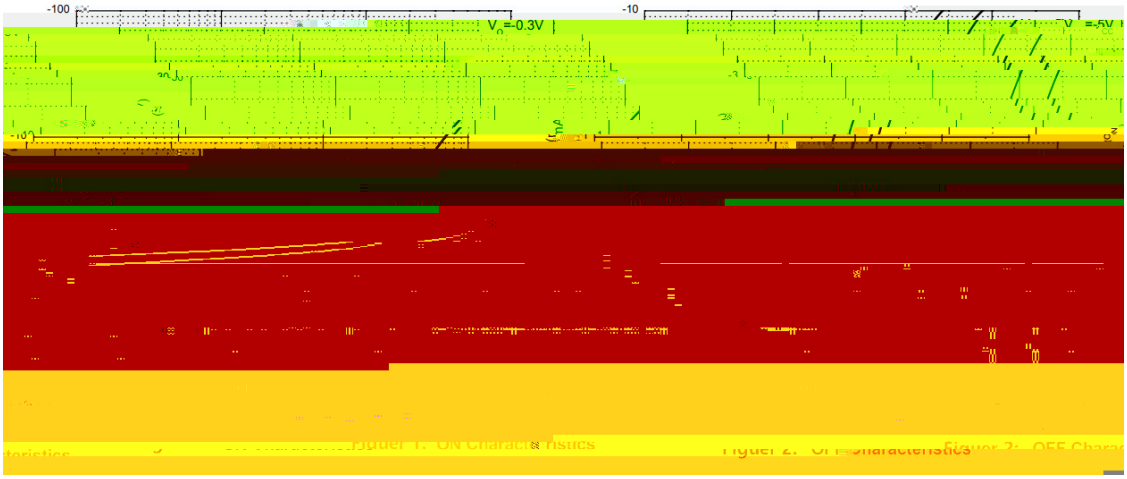


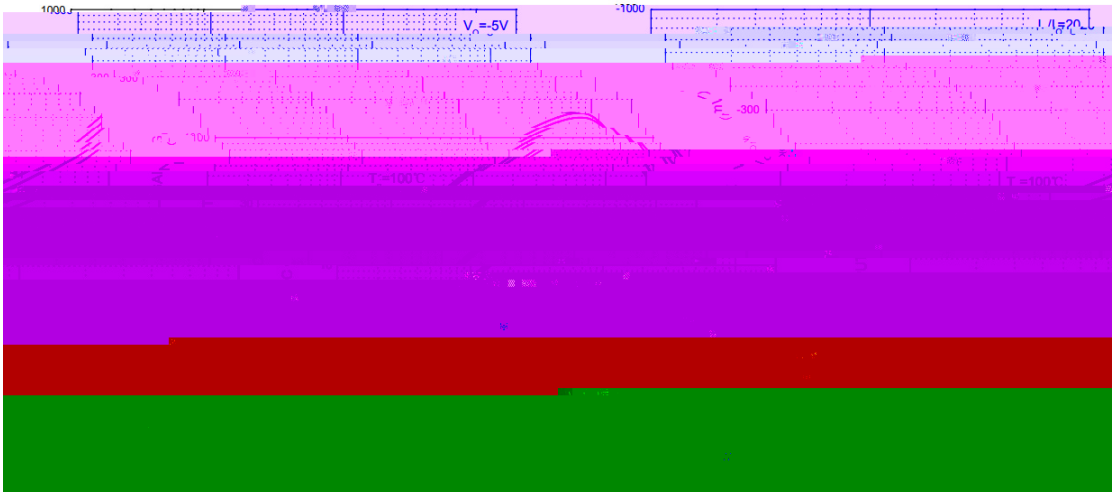
PIN 1 χ Base PIN 2 χ Emitter PIN 3 χ Collector

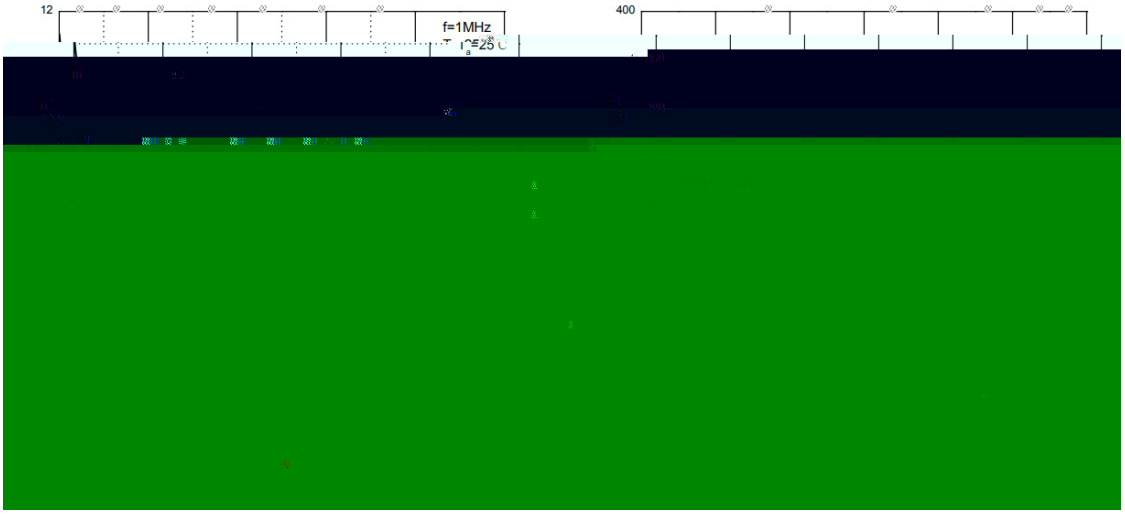
Marking	H13

v ̈Ọ Parameter	↿ N Symbol	̈Ọ Ë Rating	D Ꮋ Unit
Output Voltage	V_{CC}	-50	V
Input Voltage	V_{IN}	10	V
		-30	V
Output Current	I_O	-100	mA
Power Dissipation	P_d	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

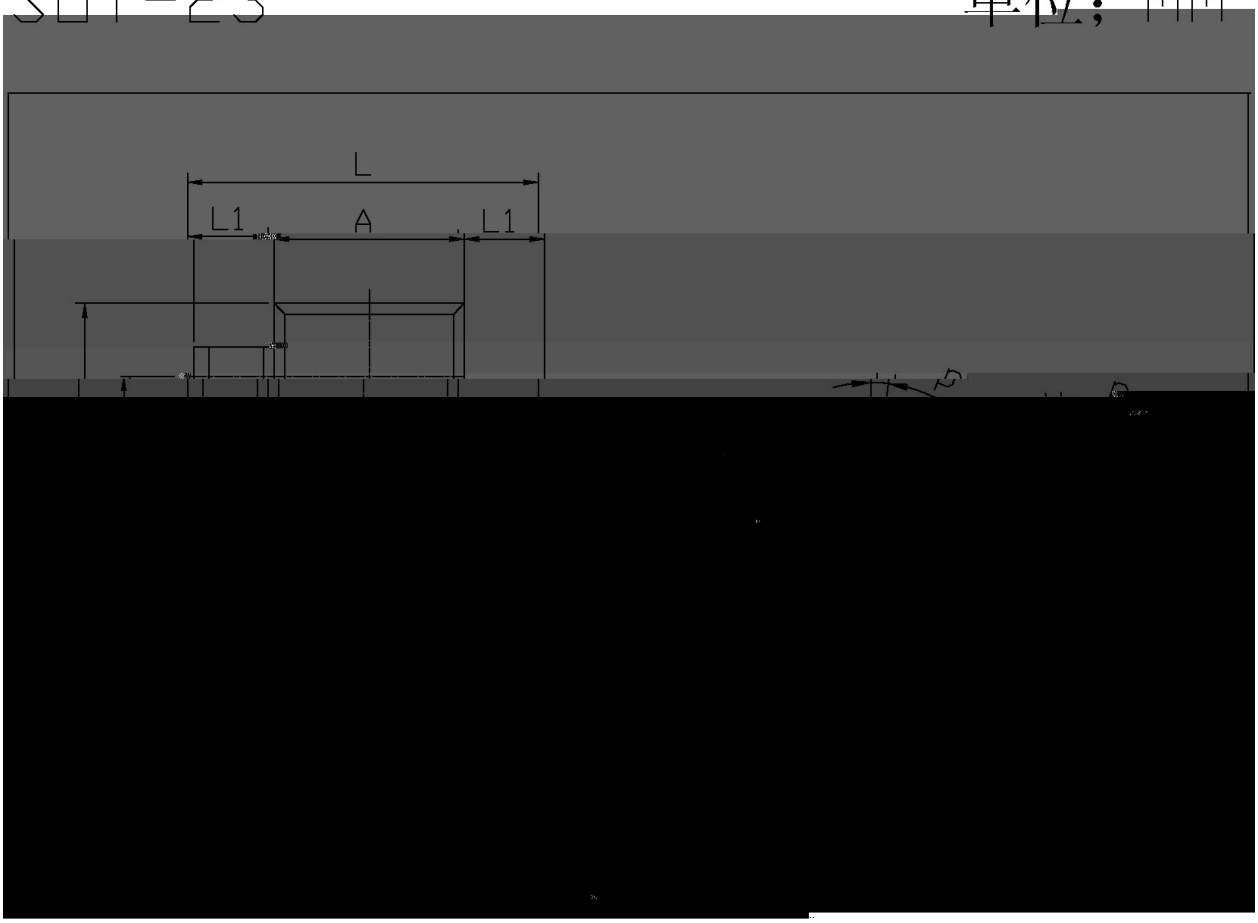
v ̈Ọ Parameter	↿ N Symbol	⅄ ; ⅂ Ꞇ Test Conditions	ώ ṇ Ë Min	Ɛ ʒ Ë Typ	ώ ᶻ Ë Max	D Ꮋ Unit
Input Voltage	$V_{I(off)}$	v_{CC}=-5.0V I_O=-100μA	-0.5		-	V
	$V_{I(on)}$	V_O=-0.3V I_O=-20mA			-3	V
Output Voltage	$V_{O(on)}$	I_O=-10mA I_I=-0.5mA		-0.1	-0.3	V
Input Current	I_I	V_I=-5.0V			-1.8	mA
Output Cut-off Current	$I_{O(off)}$	V_{CC}=-50V V_I=0V			-0.5	μA
DC Current Gain	G_I	V				

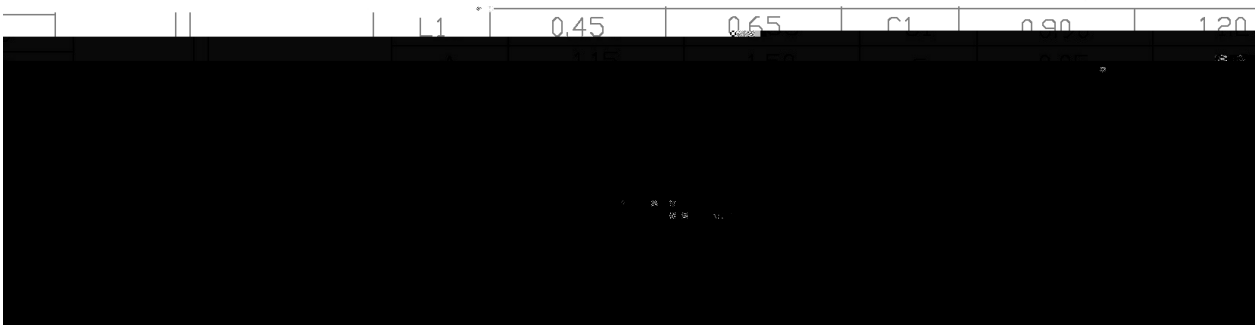

-100
-10
V_GS=-0.3V

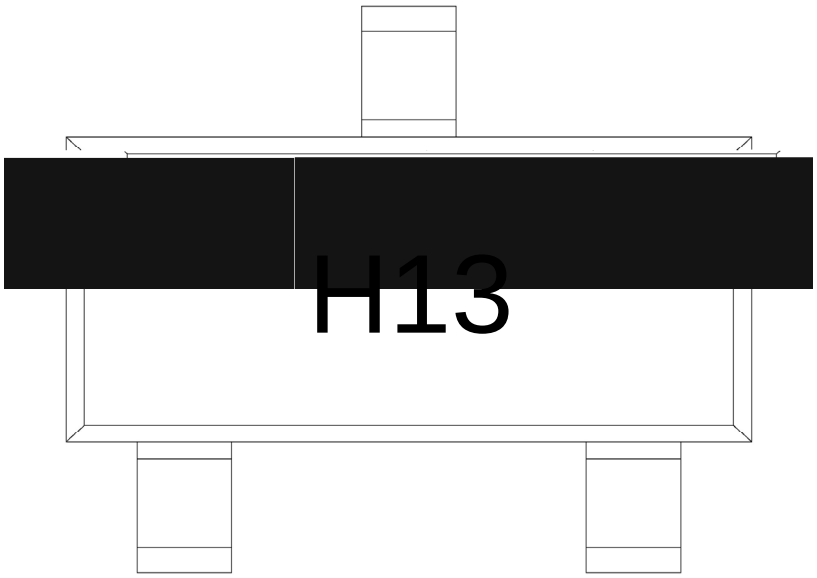

-1000
-1000
V_GS=-5V
T=100℃


12
400
f=1MHz

SOT-23 单位：mm







ᄂ ᄇ χ

K χ ㅱ ᄒ ᄋ ᄀᄇ

13 χ ㅱ ᄀ ᄂ ᄀᄇ

Note:

K χ Company Code

13 χ Product Type Code

ب ˝ χ

1 Ĺ ♬ □ ỷ 150 Ḱ 180 ł ı `H ژ 60 Ḱ 90sec;

2 Š Ө □ ỷ 245 ° 5 ł ı `H ژ 'Y ﾊ ㎞ 5 ° 0.5sec;

3 ì ˙ ﾘ ˛ ɔ ﻩ ỷ ㎞ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:150~180 ł , Time:60~90sec.

2.Peak Temp.:245 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

605 ° 5 ł (/ -5.7(Packagling)24286(SPEC.( )]TJ/TT7 1 Tf03.4485 32.3713 TD.0004 Tc-35.65309:6025130